

ZXTP25020CFH

20V, SOT23, PNP medium power transistor

Summary

$BV_{CEO} > -20V$

$BV_{ECO} > -7V$

$I_{C(\text{cont})} = -4A$

$R_{CE(\text{sat})} = 34m\Omega$

$V_{CE(\text{sat})} < -55mV @ 1A$

$P_D = 1.25W$

Complementary part number ZXTN25020CFH

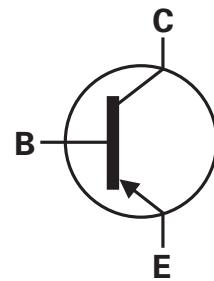


Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

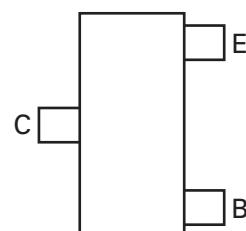
Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 7V reverse blocking voltage



Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020CFHTA	7	8	3,000

Device marking

1B2

ZXTP25020CFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	-7	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(b)	I_C	-4	A
Peak pulse current	I_{CM}	-10	A
Base current	I_B	-1	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a)	P_D	0.73	W
Linear derating factor		5.84	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b)	P_D	1.05	W
Linear derating factor		8.4	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c)	P_D	1.25	W
Linear derating factor		9.6	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d)	P_D	1.81	W
Linear derating factor		14.5	$\text{mW}/^\circ\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

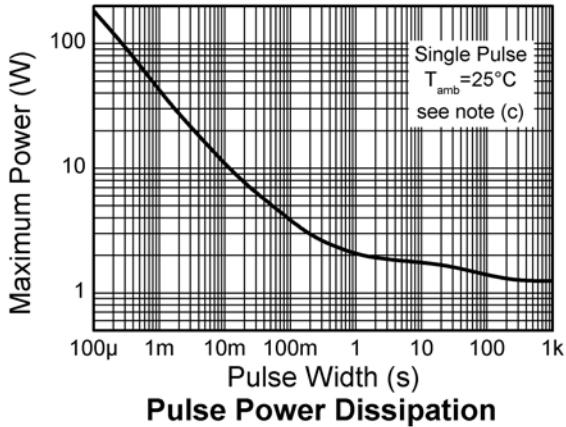
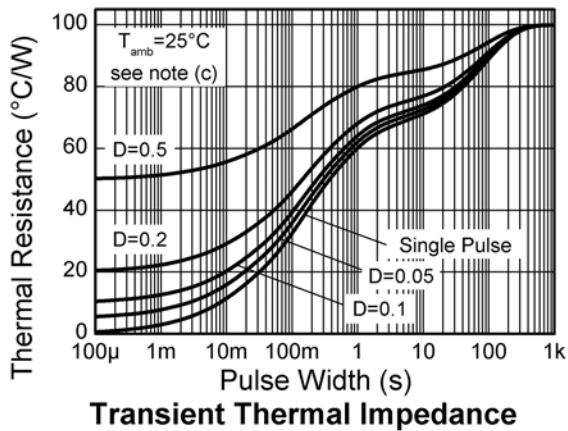
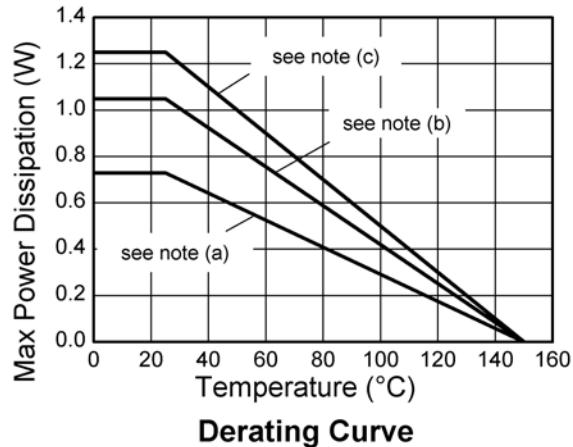
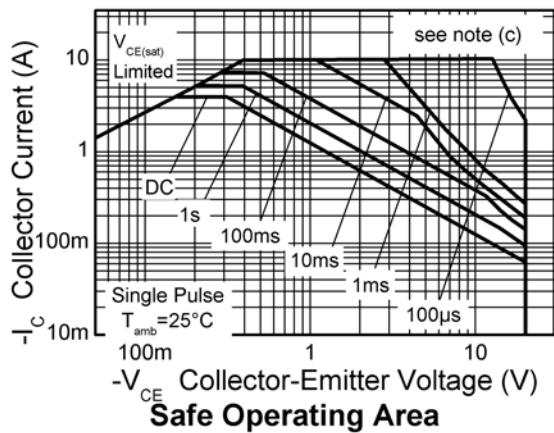
Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	171	$^\circ\text{C}/\text{W}$
Junction to ambient ^(b)	$R_{\Theta JA}$	119	$^\circ\text{C}/\text{W}$
Junction to ambient ^(c)	$R_{\Theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction to ambient ^(d)	$R_{\Theta JA}$	69	$^\circ\text{C}/\text{W}$

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at $t < 5$ secs.

Characteristics



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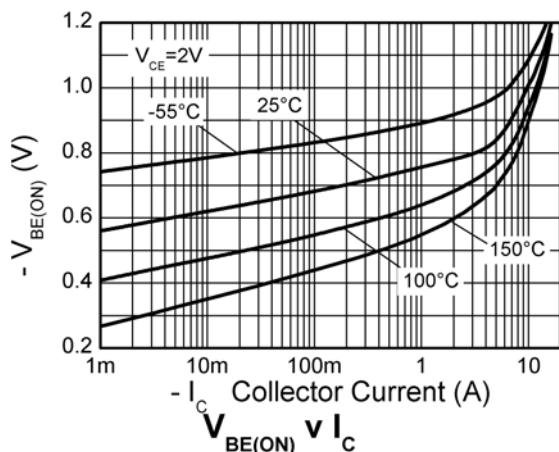
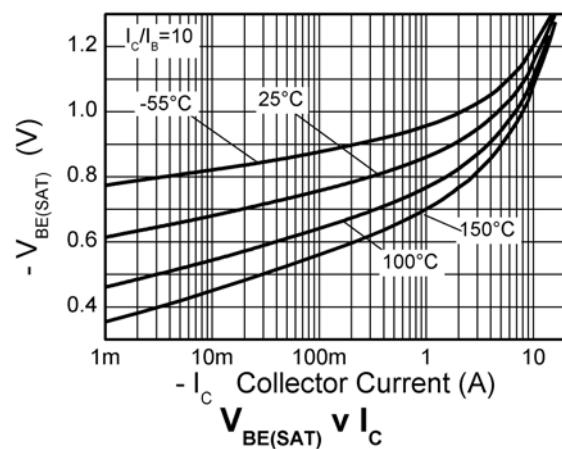
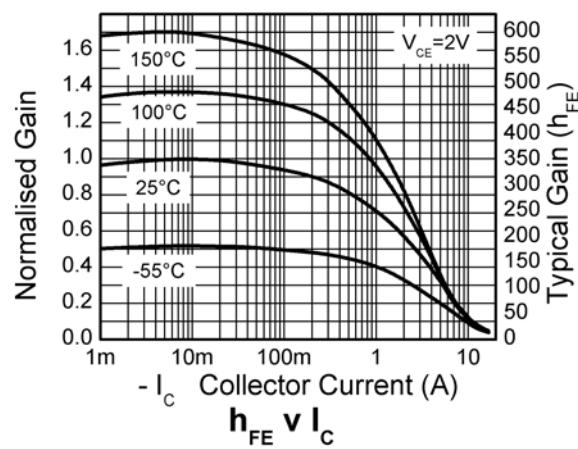
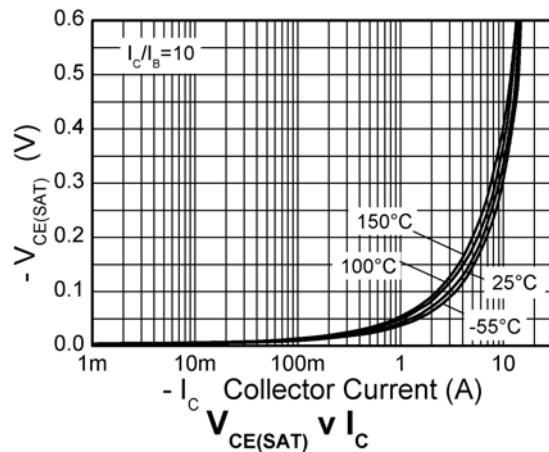
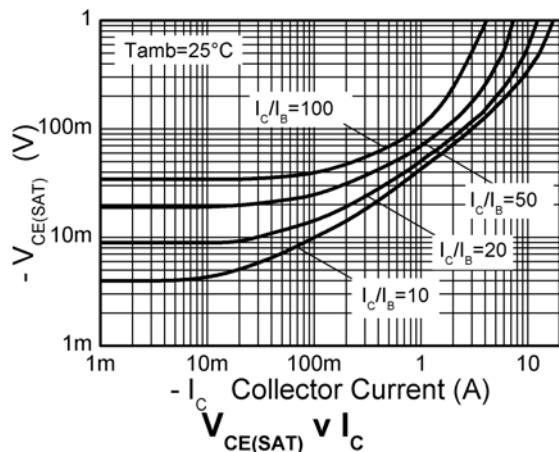
Electrical characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-25	-50		V	$I_C = -100\mu A$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-20	-35		V	$I_C = -10mA$ (*)
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu A$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	-7	-8.0		V	$I_E = -100\mu A$ (*) $R_{BC} < 10k\Omega$ or $-0.25 < V_{BC} < 0.25V$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	-7	-8.8		V	$I_E = -100\mu A$ (*)
Collector-base cut-off current	I_{CBO}		<-1	-50 -20	nA μA	$V_{CB} = -20V$ $V_{CB} = -20V, T_{amb} = 100^\circ C$
Emitter-base cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-43 -70 -120 -150	-55 -100 -170 -210	mV	$I_C = -1A, I_B = -100mA$ (*) $I_C = -1A, I_B = -20mA$ (*) $I_C = -2A, I_B = -40mA$ (*) $I_C = -4A, I_B = -200mA$ (*)
Base-emitter saturation voltage	$V_{BE(sat)}$		-930	-1050	mV	$I_C = -4A, I_B = -200mA$ (*)
Base-emitter turn-on voltage	$V_{BE(on)}$		-810	-900	mV	$I_C = -4A, V_{CE} = -2V$ (*)
Static forward current transfer ratio	h_{FE}	200 150 85	350 250 140 40	500		$I_C = -10mA, V_{CE} = -2V$ (*) $I_C = -1A, V_{CE} = -2V$ (*) $I_C = -4A, V_{CE} = -2V$ (*) $I_C = -10A, V_{CE} = -2V$ (*)
Transition frequency	f_T		285		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Output capacitance	C_{OBO}		32.4	40	pF	$V_{CB} = -10V, f = 1MHz$ (*)
Delay time	t_d		38.4		ns	$V_{CC} = -15V$
Rise time	t_r		49.2		ns	$I_C = -750mA$
Storage time	t_s		168		ns	$I_{B1} = I_{B2} = -15mA$
Fall time	t_f		55		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

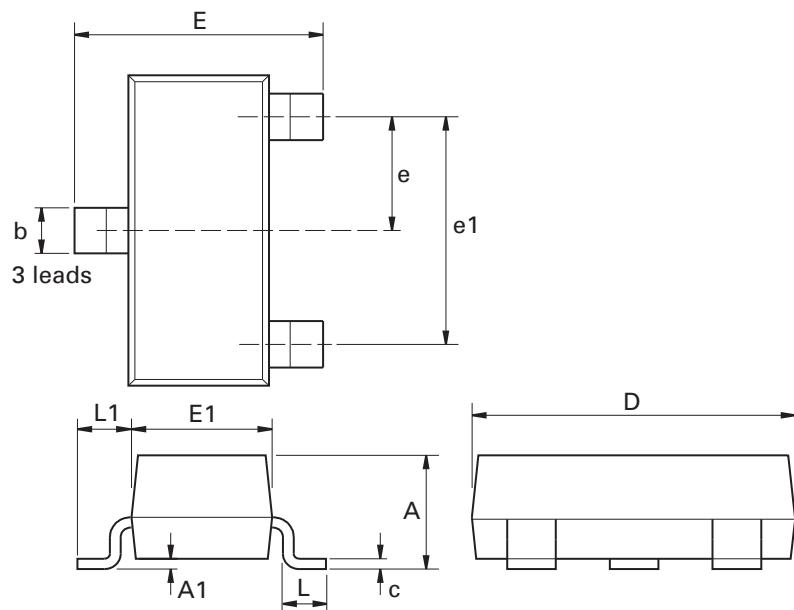
Typical characteristics



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ZXTP25020CFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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